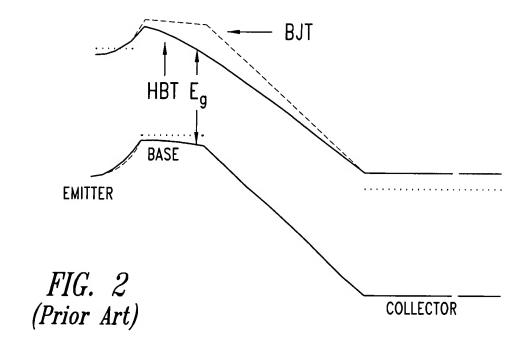
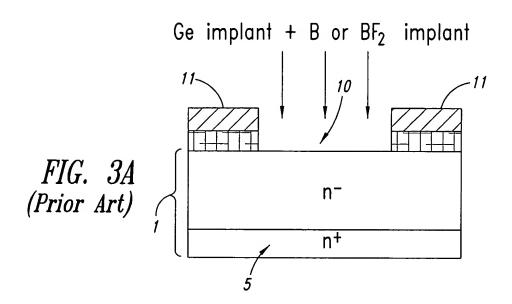
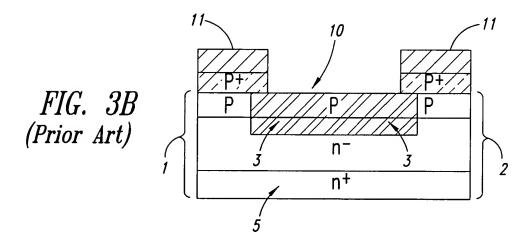
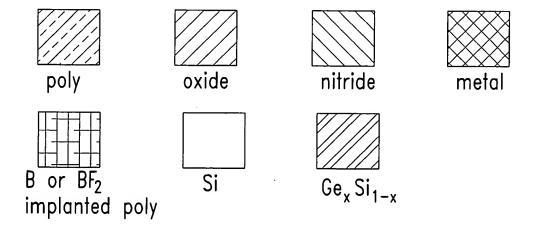


FIG. 1 (Prior Art)

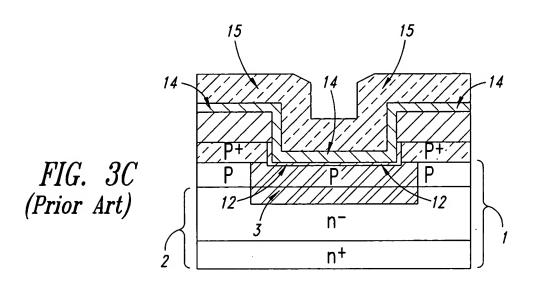


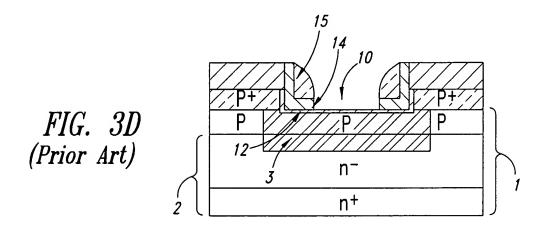


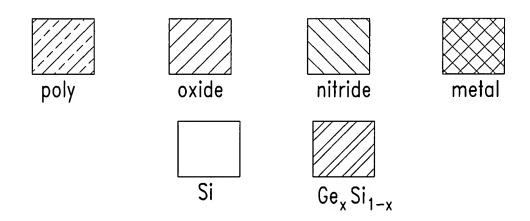




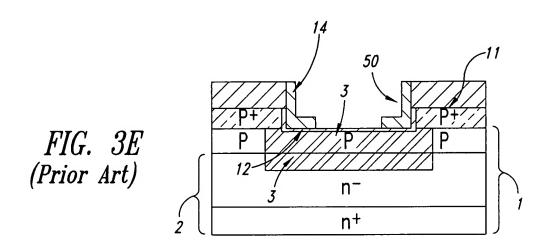
Title: A GERMANIUM IMPLANTED HBT BIPOLAR TRANSISTOR

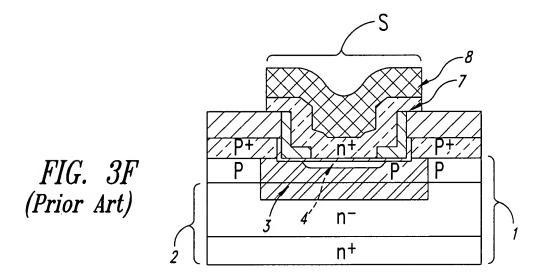


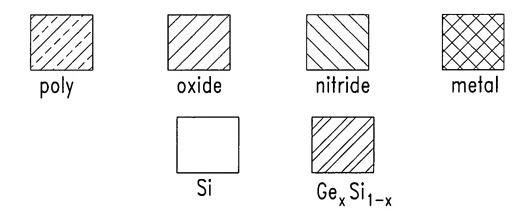




Title: A GERMANIUM IMPLANTED HBT BIPOLAR TRANSISTOR







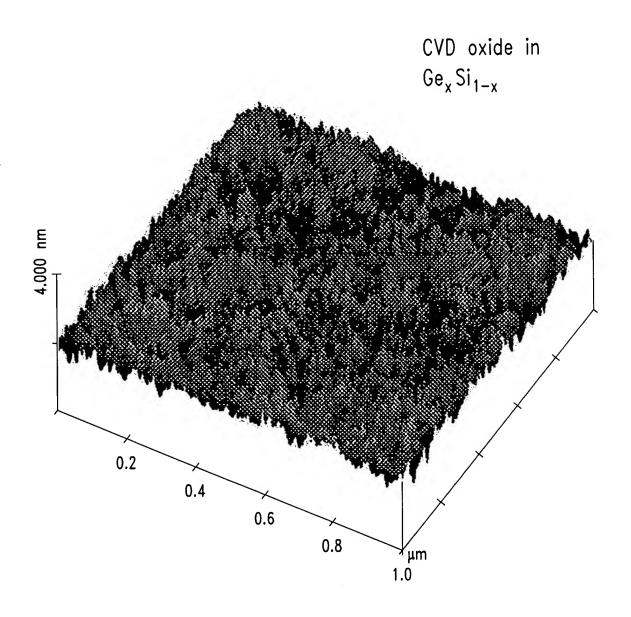


FIG. 10

Title: A GERMANIUM IMPLANTED HBT BIPOLAR TRANSISTOR
Inventor(s): Salvatore Lombardo et al. Express Mail No. EV336599567US Docket No. 856063.547D1

T1: 2 X 7.4 μm²
---- T2: 0.4 X 7.4 μm²

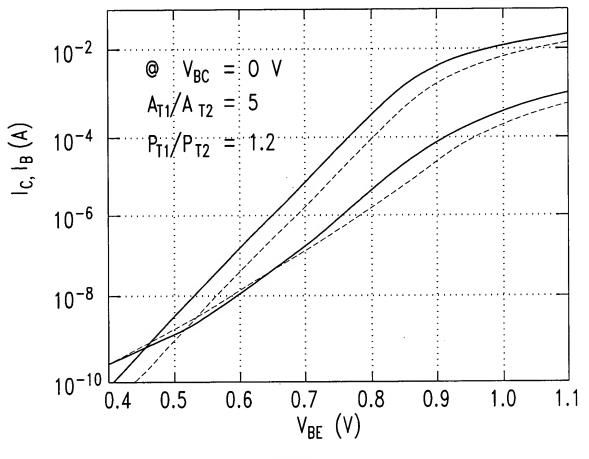
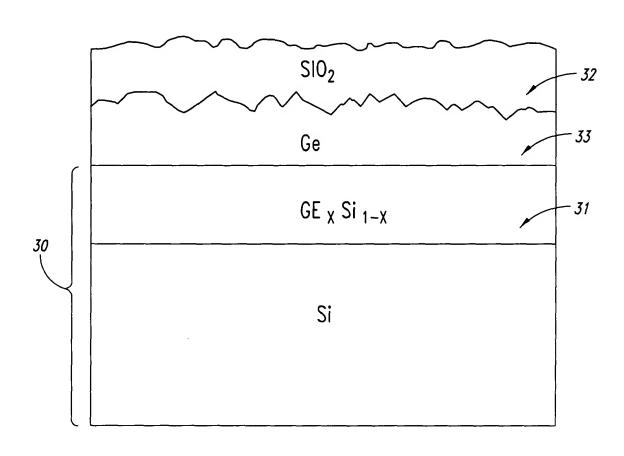


FIG. 4



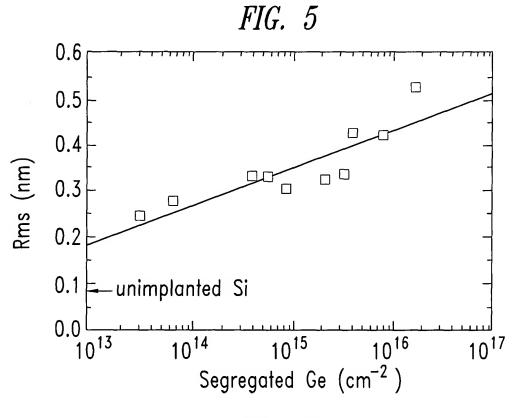


FIG. 7

Thermal oxide in Ge_xSi_{1-x}

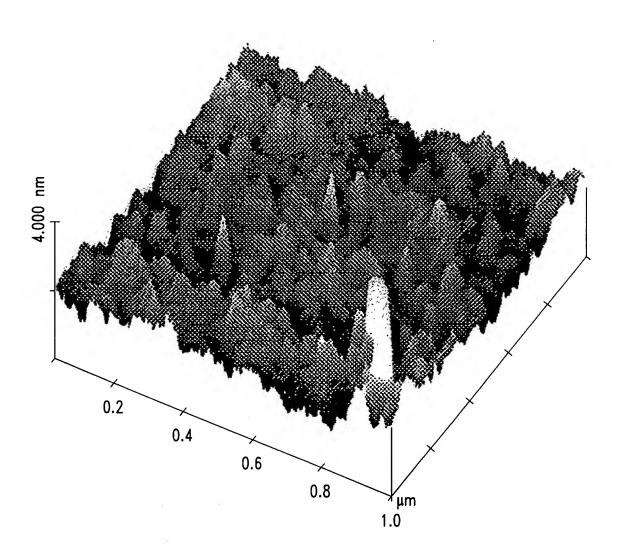
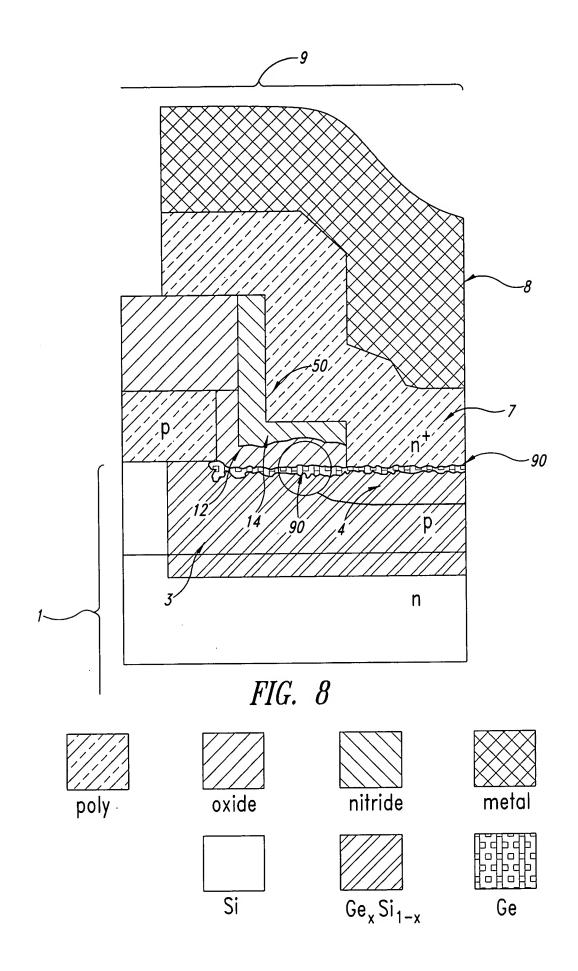


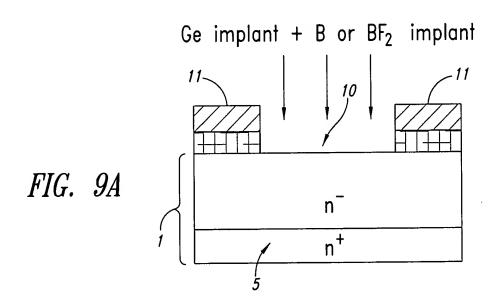
FIG. 6

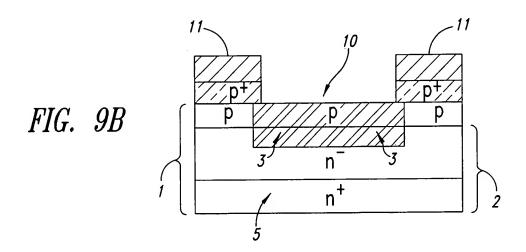
poly

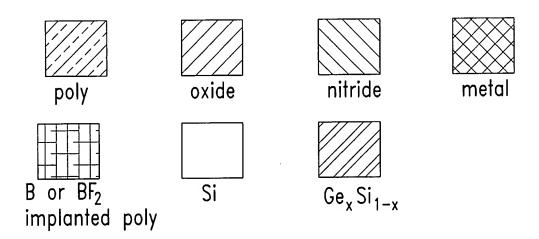
Title: A GERMANIUM IMPLANTED HBT BIPOLAR TRANSISTOR
Inventor(s): Salvatore Lombardo et al. Express Mail No. EV336599567US Docket No. 856063.547D1



Title: A GERMANIUM IMPLANTED HBT BIPOLAR TRANSISTOR
Inventor(s): Salvatore Lombardo et al. Express Mail No. EV336599567US Docket No. 856063.547D1

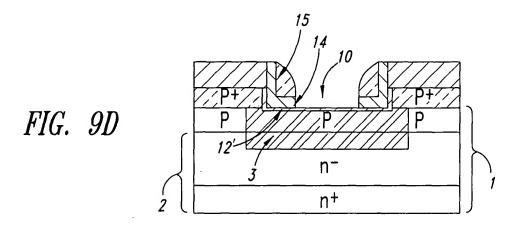


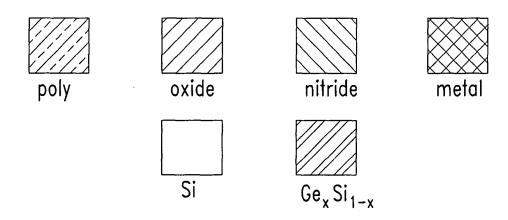




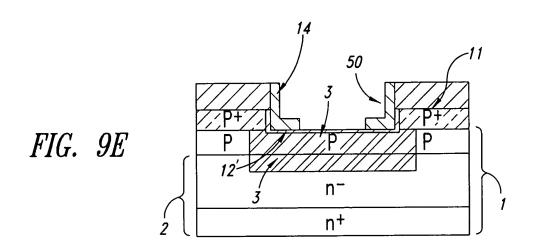
Title: A GERMANIUM IMPLANTED HBT BIPOLAR TRANSISTOR
Inventor(s): Salvatore Lombardo et al. Express Mail No. EV336599567US Docket No. 856063.547D1

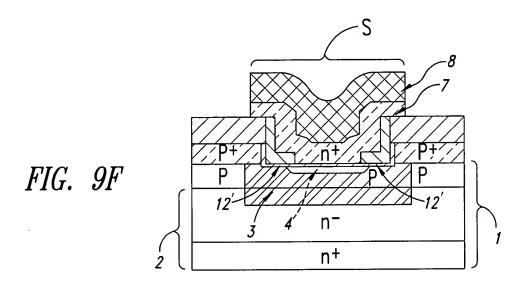
n+

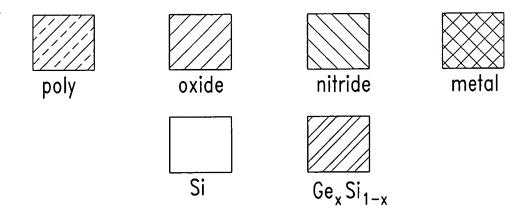




Title: A GERMANIUM IMPLANTED HBT BIPOLAR TRANSISTOR







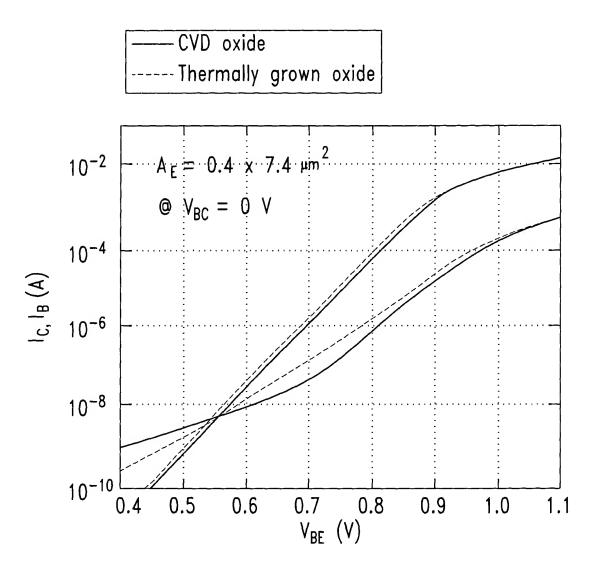
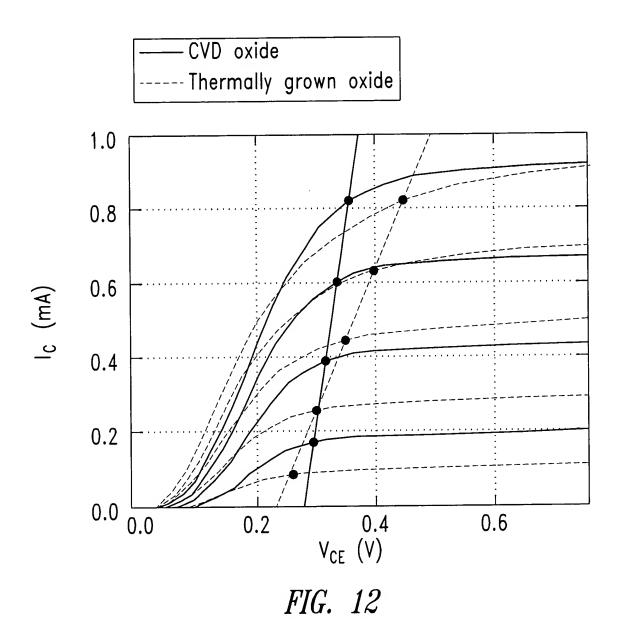


FIG. 11



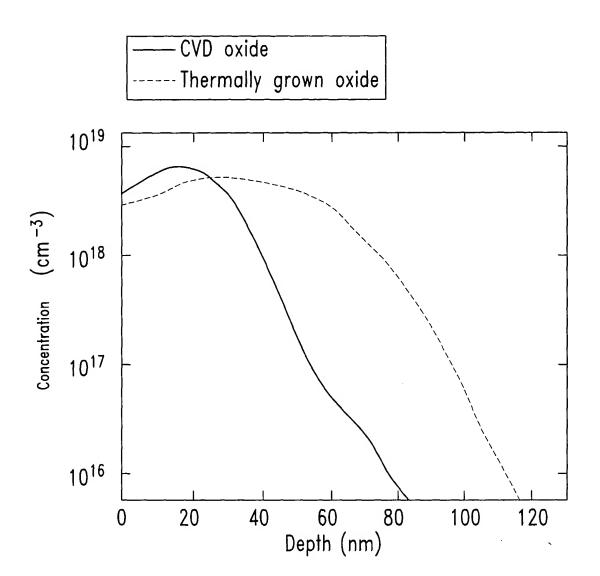


FIG. 13

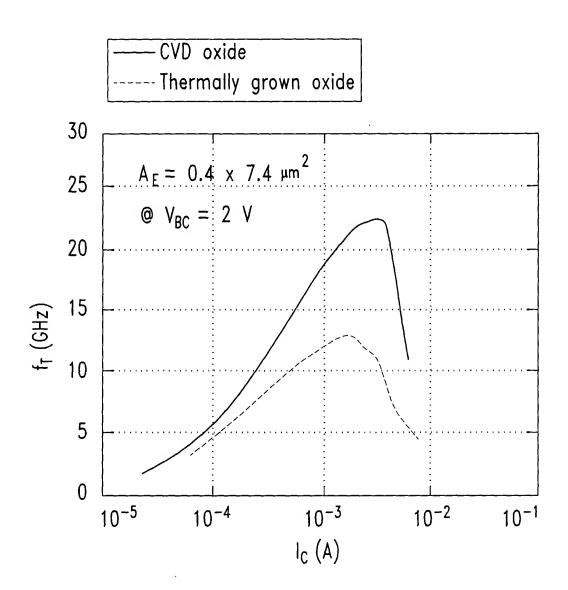


FIG. 14